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Sommario/riassunto

Major benefits to system architecture would result if cooling systems for components could be eliminated without compromising performance. This book surveys the state-of-the-art for the three major wide bandgap materials (silicon carbide, nitrides, and diamond), assesses the national and international efforts to develop these materials, identifies the technical barriers to their development and manufacture, determines the criteria for successfully packaging and integrating these devices into existing systems, and recommends future research priorities.
